

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

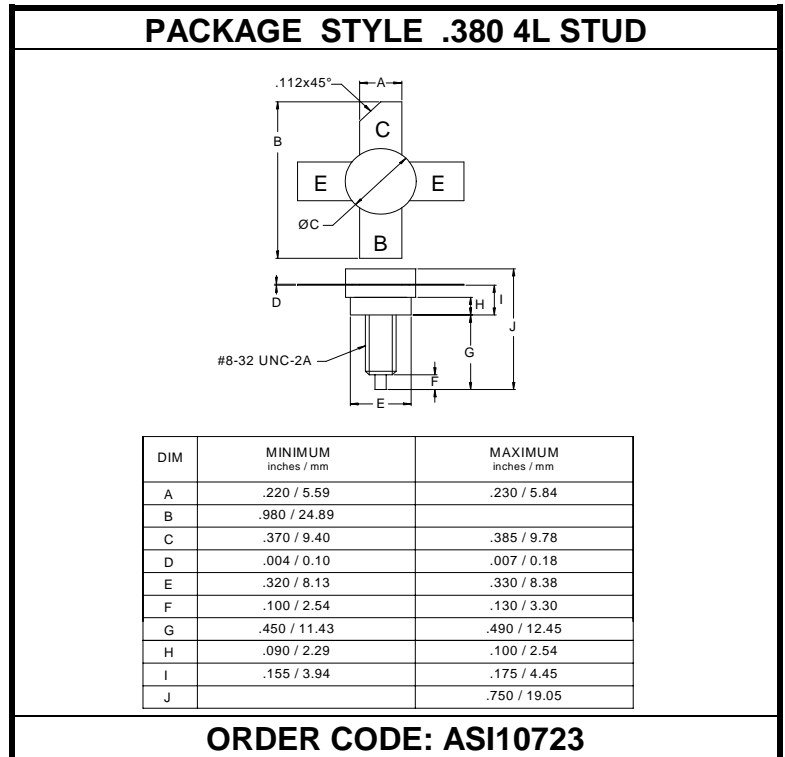
The **ASI VHB10-28S** is Designed for Class C, 28 V High Band Applications up to 175 MHz.

FEATURES:

- Common Emitter
- $P_G = 10$ dB at 10W/175 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	1.0 A
V_{CBO}	65 V
V_{CEO}	35 V
V_{CES}	65 V
V_{EBO}	4.0 V
P_{DISS}	13.0 W
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	5.5 °C/W


CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 200$ mA	65			V
BV_{CES}	$I_C = 200$ mA	65			V
BV_{CEO}	$I_C = 200$ mA	35			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CBO}	$V_{CB} = 30$ V			1.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 200$ mA	5.0		---	---
C_{ob}	$V_{CB} = 28$ V $f = 1.0$ MHz			15	pF
P_G η_C	$V_{CC} = 28$ V $P_{OUT} = 10$ W $f = 175$ MHz	10	60		dB %

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.